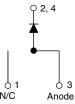
VS-HFA04SD60SHM3

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HEXFRED[®], Ultrafast Soft Recovery Diode, 4 A



www.vishay.com



TO-252AA (D-PAK
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PRODUCT SUMMARY						
Package	TO-252AA (D-PAK)					
I _{F(AV)}	4 A					
V _R	600 V					
V _F at I _F	1.4 V					
t _{rr} typ.	17 ns					
T _J max.	150 °C					
Diode variation	Single die					

FEATURES

- Ultrafast recovery time
- Ultrasoft recovery
- Very low I_{RRM} Very low Q_{rr}
- · Guaranteed avalanche
- Specified at operating temperature
- AEC-Q101 qualified
- Meets JESD 201 class 2 whisker test
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION / APPLICATIONS

These diodes are optimized to reduce losses and EMI / RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for freewheeling, flyback, power converters, motor drives, and other applications where high speed and reduced switching losses are design requirements.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V _{RRM}		600	V		
Maximum continuous forward current	I _{F(AV)}	T _C = 100 °C	4			
Single pulse forward current	I _{FSM}		25	А		
Repetitive peak forward current	I _{FRM}	T _C = 116 °C	16			
Maximum power dissipation	PD	T _C = 100 °C	10	W		
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +150	°C		





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ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-			
_		$I_F = 4 A$	-	1.5	1.8	V		
Forward voltage V _F	I _F = 8 A	-	1.8	2.2				
000 ligi l		I _F = 4 A, T _J = 125 °C	-	1.4	1.7			
Maximum reverse		V _R = V _R rated	-	0.17	3.0			
leakage current	I _R	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	-	44	300	μA		
Junction capacitance	CT	V _R = 200 V		4	8	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

DYNAMIC RECOVERY CHARACTERISTICS ($T_C = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ J}$	A/μA, V _R = 30 V	-	17	-		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	28	42	ns	
		T _J = 125 °C	I _F = 4 A dI _F /dt = 200 A/μs V _R = 200 V	-	38	57		
Peak recovery current	I _{RRM}	T _J = 25 °C		-	2.9	5.2	А	
Teak recovery current		T _J = 125 °C		-	3.7	6.7	~	
Reverse recovery charge	0	T _J = 25 °C		-	40	60	nC	
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	70	105	no	
Rate of fall of recovery current	t dl /dt	T _J = 25 °C		-	280	-	A∕µs	
Rate of fall of recovery current dl _{(rec)M} /dt		T _J = 125 °C		-	235	-	γγµs	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	150	°C		
Thermal resistance, junction to case	R _{thJC}		-	-	5.0	°C/W		
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	0/10		
Weight			-	2.0	-	g		
weight			-	0.07	-	oz.		
Mounting torque				-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style TO-252AA (D-PAK)	HFA04SD60SH					

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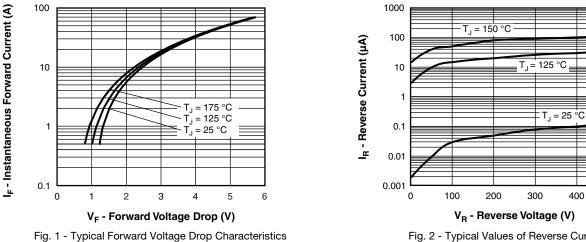


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

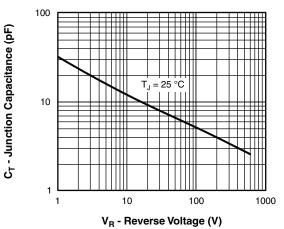


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

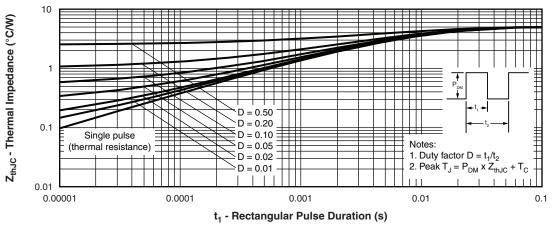


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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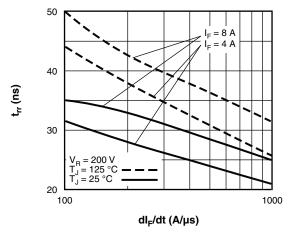
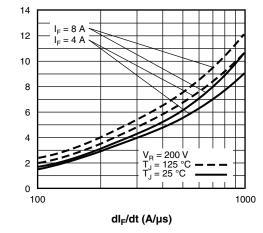


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

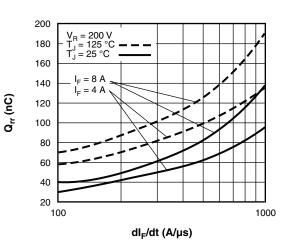


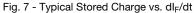
I_{RR} (A)

Fig. 6 - Typical Recovery Current vs. dl_F/dt

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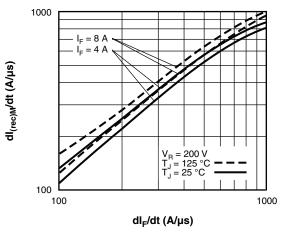


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt

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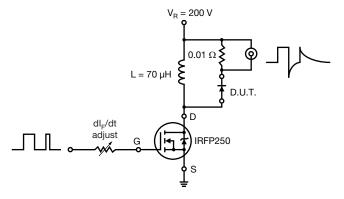
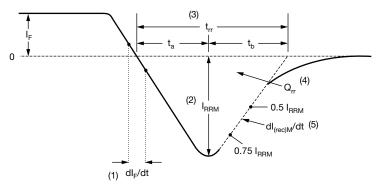


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (5) dl_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}

 $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$

Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

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Device code	vs-	HF	Α	04	SD	60	S	TR	н	М3
		(2)	(3)	(4)	(5)	(6)	(7)	(8)	(9)	(10)
	_	Ŭ	Ŭ	U	U	U	U	Ŭ	U	Ŭ
	1 -	Vish	ay Sem	iconduc	tors pro	duct				
	2 -	HEX	(FRED®	family						
	3 -	Elec	Electron irradiated							
	4 -	Curr	Current rating (04 = 4 A)							
	5 -	D-P/	D-PAK							
	6 -	Volta	Voltage rating (60 = 600 V)							
		S =	S = D-PAK							
	8 -	• TR	• TR = tape and reel							
			• R = tape and reel (right oriented)							
			• L = tape and reel (left oriented)							
	9 -		H = AEC-Q101 qualified							
	10 -		Environmental digit:							
				-		complia	nt, and	termina	tions lea	d (Pb)-fi

ORDERING INFORMATION (Example) **PREFERRED P/N** QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION VS-HFA04SD60SHM3 75 3000 Antistatic plastic tube VS-HFA04SD60STRHM3 2000 2000 13" diameter reel VS-HFA04SD60STRRHM3 3000 3000 13" diameter reel VS-HFA04SD60STRLHM3 3000 3000 13" diameter reel

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95519				
Part marking information	www.vishay.com/doc?95518				
Packaging information	www.vishay.com/doc?95033				



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